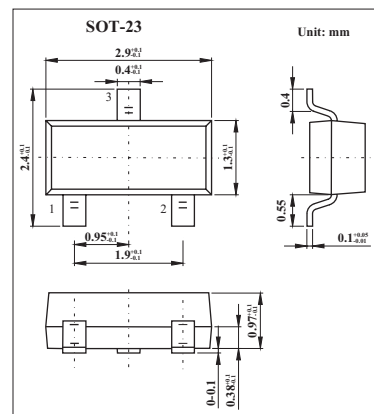


Schottky barrier (double) diodes

BAS70 series

■ Features

- Low forward current
- High breakdown voltage
- Guard ring protected
- Small plastic SMD package
- Low diode capacitance.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V_R			70	V
Continuous forward current	I_F			70	mA
Repetitive peak forward current	I_{FRM}	$t_p \leq 1 \text{ s}; \delta \leq 0.5$		70	mA
Non-repetitive peak forward current	I_{FSM}	$t_p < 10 \text{ ms}$		100	mA
Storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
Junction temperature	T_j			150	$^\circ\text{C}$
Operating ambient temperature	T_{amb}		-65	+150	$^\circ\text{C}$
thermal resistance from junction to ambient	$R_{th j-a}$			500	K/W

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Max	Unit
Forward voltage	V_F	$I_F = 1 \text{ mA}$	410	mV
		$I_F = 10 \text{ mA}$	750	mV
		$I_F = 15 \text{ mA}$	1	V
Reverse voltage leakage current	I_R	$V_R = 50 \text{ V}; \text{note 1}$	100	nA
		$V_R = 70 \text{ V}; \text{note 1}$	10	μA
Charge carrier life time (Krakauer method)	τ	$I_F = 5 \text{ mA}$	100	ps
Diode capacitance	C_d	$f = 1 \text{ MHz}; V_R = 0;$	2	pF

Note

1. Pulse test: $t_p = 300 \mu\text{s}; \delta = 0.02$

■ Marking

Type	BAS70	BAS70-04	BAS70-05	BAS70-06	BAS70-07
Marking	73*	74*	75*	76*	77p